IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicants	Johannes Kaeppeler, *et al.*
Serial No. 10/	Filing Date: October 14, 2003
Title of Application:	Method For Depositing Especially Crystalline Layers From The Gas Phase Onto Especially Crystalline Substrates

Commissioner for Patents
Post Office Box 1450
Alexandria, VA 22313-1450

Preliminary Amendment

Applicants herewith present its amendment and remarks. Please amend the claims as detailed below.

In the Claims

1. (currently amended) Device for depositing in particular crystalline layers on in particular crystalline substrates from the gas phase, which includes

a heated reaction chamber ~~(1)~~ having a substrate holder ~~(2)~~ for receiving at least one substrate ~~(3)~~;

one or more heated sources ~~(4)~~, where a gaseous halide is formed by chemical reaction of a halogen, in particular HC1, which is fed to the source together with a carrier gas, and a metal, for example Ga, In, Al, arranged at the source ~~(4)~~, the gaseous halide being conveyed through a gas inlet section ~~(5)~~ to a substrate supported by the substrate holder ~~(2)~~;

a hydride feedline ~~(6)~~ for feeding a hydride, in particular NH_3, Ash_3 or PH_3, into the reaction chamber,

characterized in that the reaction chamber, ~~(1)~~ has an axis of symmetry, and a multiplicity of rotationally driven substrate holders ~~(2)~~ are arranged annularly about the axis of symmetry on the substrate holder ~~(7)~~, the separately heatable sources being disposed in the axis of symmetry.

2. (currently amended) Method for depositing in particular crystalline layers on in particular crystalline substrates from the gas phase, which includes

a heated reaction chamber ~~(1)~~ having a substrate holder ~~(2)~~ for receiving at least one substrate ~~(3)~~;